IMPORTANT NOTICE

Dear customer,

As of December 7th, 2015 BL RF Power of NXP Semiconductors will operate as an independent company under the new trade name Ampleon, which will be used in future data sheets together with new contact details.

In data sheets, where the previous Philips references is mentioned, please use the new links as shown below.

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http://www.semiconductors.philips.com use http://www.ampleon.com (Internet)

sales.addresses@www.semiconductors.philips.com use http://www.ampleon.com/sales

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Thank you for your cooperation and understanding,

Ampleon

UHF power MOS transistor

BLF542

FEATURES

- · High power gain
- · Easy power control
- · Good thermal stability
- · Gold metallization ensures excellent reliability
- · Withstands full load mismatch
- Designed for broadband operation.

APPLICATIONS

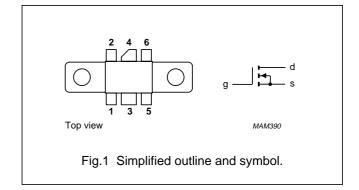
• Large signal amplifier applications in the UHF frequency range.

DESCRIPTION

N-channel enhancement mode vertical D-MOS power transistor encapsulated in a 6-lead, SOT171A flange package with a ceramic cap. All leads are isolated from the flange.

PINNING - SOT171A

| PIN | DESCRIPTION | | | |
|-----|-------------|--|--|--|
| 1 | source | | | |
| 2 | source | | | |
| 3 | gate | | | |
| 4 | drain | | | |
| 5 | source | | | |
| 6 | source | | | |



QUICK REFERENCE DATA

RF performance at T_h = 25 °C in a common source class-B circuit.

| MODE OF OPERATION | f (MHz) | V _{DS} (V) | P _L (W) | G _p (dB) | η _D (%) |
|-------------------|------------|---------------------|-----------------------|------------------------|-----------------------|
| CW, class-B | 500 | 28 | 5 | >13 | >50 |

CAUTION

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

WARNING

Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

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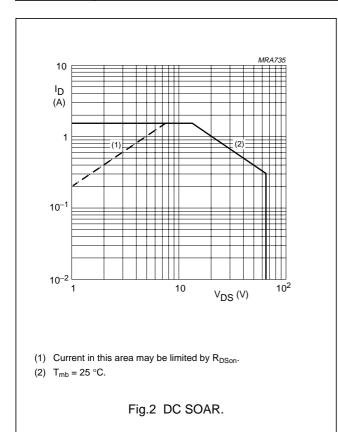
LIMITING VALUES

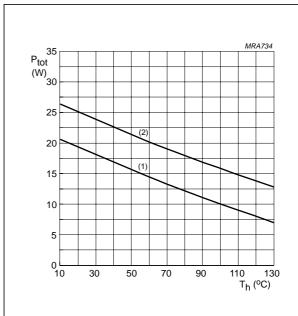
In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------|-------------------------|------|------|------|
| V _{DS} | drain-source voltage | | _ | 65 | V |
| V _{GS} | gate-source voltage | | _ | ±20 | V |
| I _D | drain current (DC) | | _ | 1.5 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C | _ | 20 | W |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | _ | 200 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | VALUE | UNIT |
|----------------------|---|-------|------|
| R _{th j-mb} | thermal resistance from junction to mounting base | 8.8 | K/W |
| R _{th mb-h} | thermal resistance from mounting base to heatsink | 0.4 | K/W |





- (1) Continuous operation.
- (2) Short time operation during mismatch.

Fig.3 Power derating curves.

UHF power MOS transistor

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CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

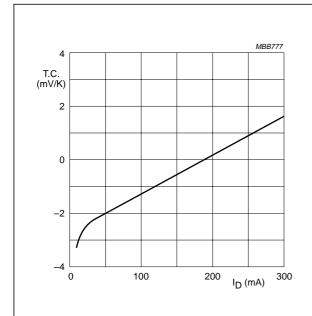
| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------------------|--------------------------------|--|------|------|------|------|
| V _{(BR)DSS} | drain-source breakdown voltage | $I_D = 0.1 \text{ mA}; V_{GS} = 0$ | 65 | _ | _ | V |
| I _{DSS} | drain-source leakage current | V _{GS} = 0; V _{DS} = 28 V | _ | _ | 10 | μΑ |
| I _{GSS} | gate-source leakage current | $V_{GS} = \pm 20 \text{ V}; V_{DS} = 0$ | _ | _ | 1 | μΑ |
| V_{GSth} | gate-source threshold voltage | $I_D = 10 \text{ mA}; V_{DS} = 10 \text{ V}$ | 2 | _ | 4.5 | V |
| 9fs | forward transconductance | I _D = 0.3 A; V _{DS} = 10 V | 160 | 240 | _ | mS |
| R _{DSon} | drain-source on-resistance | I _D = 0.3 A; V _{GS} = 15 V | _ | 3.3 | 5 | Ω |
| I _{DSX} | on-state drain current | V _{GS} = 15 V; V _{DS} = 10 V | _ | 1.4 | _ | Α |
| C _{is} | input capacitance | V _{GS} = 0; V _{DS} = 28 V; f = 1 MHz | _ | 14 | _ | pF |
| C _{os} | output capacitance | V _{GS} = 0; V _{DS} = 28 V; f = 1 MHz | _ | 9.4 | _ | pF |
| C _{rs} | feedback capacitance | V _{GS} = 0; V _{DS} = 28 V; f = 1 MHz | _ | 1.7 | _ | pF |

V_{GS} group indicator

| GROUP | | LIMITS (V) | | LIMITS (V) | | |
|-------|------|---------------|---|---------------|------|--|
| | MIN. | MAX. | | MIN. | MAX. | |
| Α | 2.0 | 2.1 | 0 | 3.3 | 3.4 | |
| В | 2.1 | 2.2 | Р | 3.4 | 3.5 | |
| С | 2.2 | 2.3 | Q | 3.5 | 3.6 | |
| D | 2.3 | 2.4 | R | 3.6 | 3.7 | |
| E | 2.4 | 2.5 | S | 3.7 | 3.8 | |
| F | 2.5 | 2.6 | Т | 3.8 | 3.9 | |
| G | 2.6 | 2.7 | U | 3.9 | 4.0 | |
| Н | 2.7 | 2.8 | V | 4.0 | 4.1 | |
| J | 2.8 | 2.9 | W | 4.1 | 4.2 | |
| K | 2.9 | 3.0 | Х | 4.2 | 4.3 | |
| L | 3.0 | 3.1 | Y | 4.3 | 4.4 | |
| М | 3.1 | 3.2 | Z | 4.4 | 4.5 | |
| N | 3.2 | 3.3 | | | | |

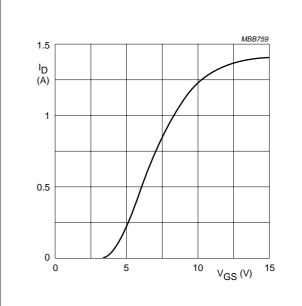
UHF power MOS transistor

BLF542



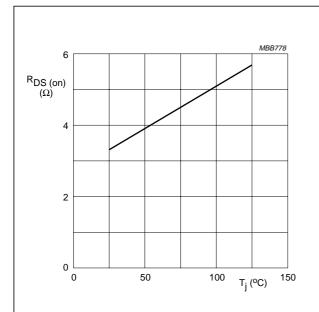
 $V_{DS} = 10 \text{ V}.$

Fig.4 Temperature coefficient of gate-source voltage as a function of drain current; typical values.



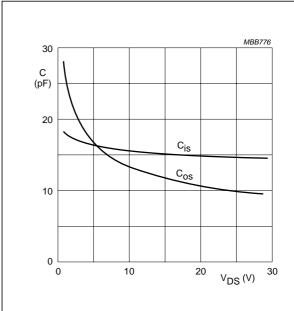
 V_{DS} = 10 V; T_j = 25 °C.

Fig.5 Drain current as a function of gate-source voltage; typical values.



 $I_D = 0.3 A$; $V_{GS} = 15 V$

Fig.6 Drain-source on-resistance as a function of junction temperature; typical values.

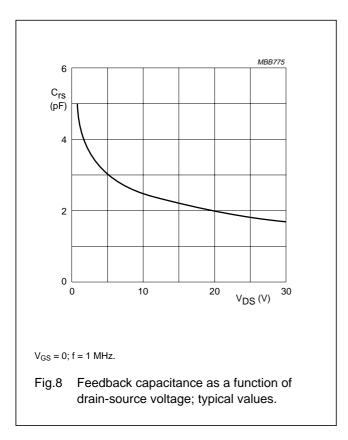


 $V_{GS} = 0$; f = 1 MHz.

Fig.7 Input and output capacitance as functions of drain-source voltage; typical values.

UHF power MOS transistor

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APPLICATION INFORMATION FOR CLASS-B OPERATION

 T_{mb} = 25 °C unless otherwise specified.

RF performance in CW operation in a common source class-B test circuit.

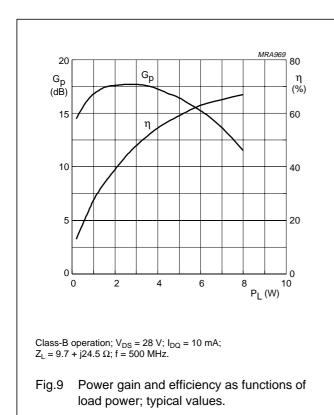
| MODE OF OPERATION | f (MHz) | V _{DS} (V) | I _{DQ} (mA) | P _L (W) | G _P (dB) | η _D (%) |
|-------------------|------------|---------------------|-------------------------|-----------------------|------------------------|-----------------------|
| CW, class-B | 500 | 28 | 50 | 5 | >13 typ. 16.5 | >50 typ. 59 |

Ruggedness in class-B operation

The BLF542 is capable of withstanding a full load mismatch corresponding to VSWR = 50:1 through all phases under the following conditions: $V_{DS} = 28 \text{ V}$; f = 500 MHz at rated output power.

UHF power MOS transistor

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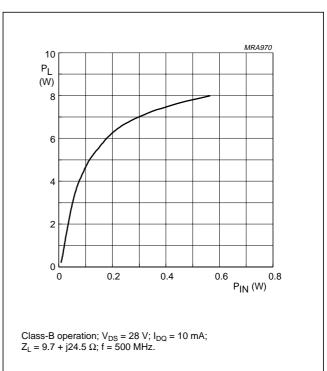
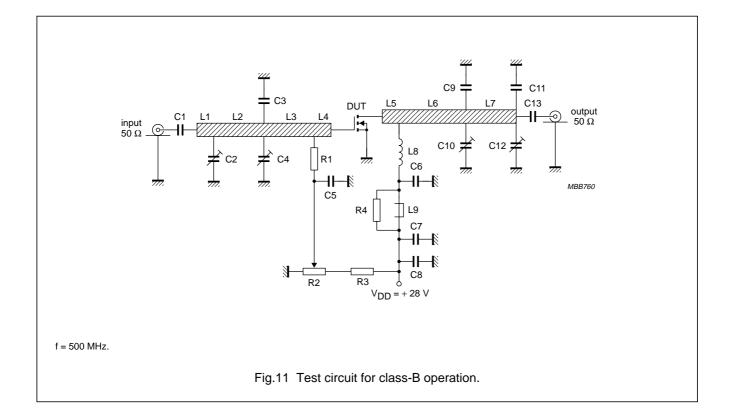


Fig.10 Load power as a function of input power; typical values.



UHF power MOS transistor

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List of components (see Fig.11)

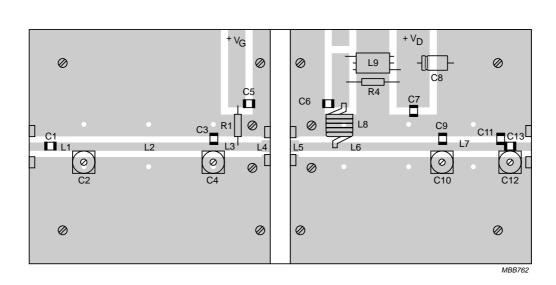
| COMPONENT | DESCRIPTION | VALUE | DIMENSIONS | CATALOGUE NO. |
|---------------------|---|---------------|---|----------------|
| C1, C5, C13 | multilayer ceramic chip capacitor; note 1 | 390 pF | | |
| C2, C4, C10, C12 | film dielectric trimmer | 2 to 18 pF | | 222 809 05217 |
| C3, C9 | multilayer ceramic chip capacitor; note 1 | 39 pF | | |
| C6 | multilayer ceramic chip capacitor; note 2 | 220 pF | | |
| C7 | multilayer ceramic chip capacitor | 100 nF | | 2222 852 47104 |
| C8 | electrolytic capacitor | 63 V, 10 μF | | 2222 030 28109 |
| C11 | multilayer ceramic chip capacitor; note 1 | 10 pF | | |
| L1 | stripline; note 3 | 50 Ω | 11 mm × 2.5 mm | |
| L2 | stripline; note 3 | 50 Ω | 37 mm × 2.5 mm | |
| L3 | stripline; note 3 | 50 Ω | 13 mm × 2.5 mm | |
| L4, L5 | stripline; note 3 | 42 Ω | 3 mm × 3 mm | |
| L6 | stripline; note 3 | 50 Ω | 39 mm × 2.5 mm | |
| L7 | stripline; note 3 | 50 Ω | 22 mm × 2.5 mm | |
| L8 | 8 turns 0.8 mm enamelled copper wire | 250 nH | length 9 mm int. dia. 6 mm leads 2 × 5 mm | |
| L9 | grade 3B Ferroxcube wideband RF choke | | | 4312 020 36640 |
| R1 | metal film resistor | 10 kΩ, 0.4 W | | 2322 151 71003 |
| R2 | 10 turn potentiometer | 50 kΩ | | |
| R3 | metal film resistor | 205 kΩ, 0.4 W | | 2322 151 72054 |
| R4 | metal film resistor | 10 Ω, 0.4 W | | 2322 151 71009 |

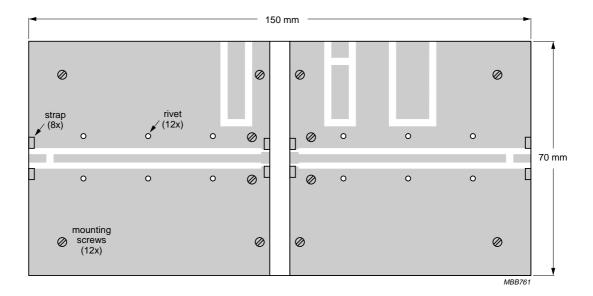
Notes

- 1. American Technical Ceramics (ATC) capacitor, type 100A or other capacitor of the same quality.
- 2. American Technical Ceramics (ATC) capacitor, type 100B or other capacitor of the same quality.
- 3. The striplines are on a double copper-clad printed circuit board with PTFE fibre-glass dielectric (ϵ_r = 2.2); thickness $1/_{32}$ inch.

UHF power MOS transistor

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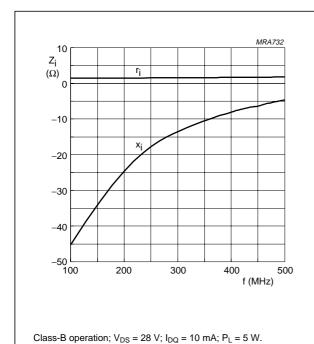


The components are mounted on one side of a copper-clad printed circuit board; the other side is unetched and serves as a ground plane. Earth connections from the component side to the ground plane are made by means of fixing screws, hollow rivets and copper foil straps, as shown.

Fig.12 Component layout for 500 MHz test circuit.

UHF power MOS transistor

BLF542



Oldoo B opolation, V_{DS} = 20 V, I_{DQ} = 10 m/V, I_C = 0 VV.

Fig.13 Input impedance as a function of frequency (series components); typical values.

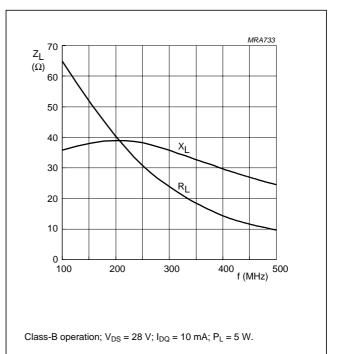
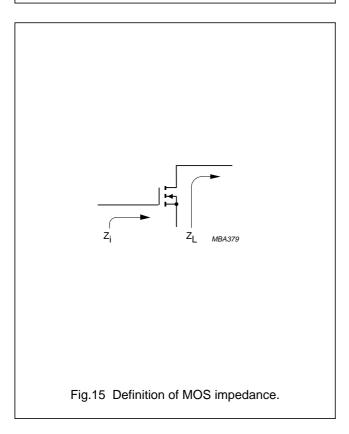
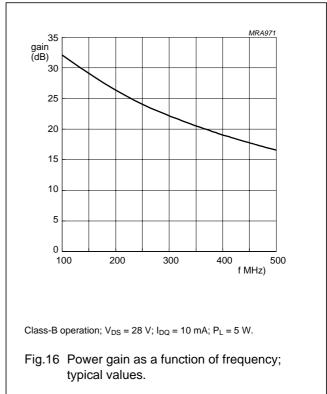


Fig.14 Load impedance as a function of frequency (series components); typical values.





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UHF power MOS transistor

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BLF542 scattering parameters

 $V_{DS} = 28 \text{ V}; I_D = 10 \text{ mA}; \text{ note 1}$

| f (MU=) | f (MHz) | | S | 21 | s ₁ | 2 | s ₂₂ | | |
|-----------|-----------------|--------|-----------------|-------|-----------------|-------|-----------------|--------|--|
| 1 (WIT12) | s ₁₁ | ∠Φ | s ₂₁ | ∠Φ | s ₁₂ | ∠Φ | s ₂₂ | ∠Φ | |
| 5 | 1.00 | -3.0 | 5.88 | 178.0 | 0.00 | 0.0 | 1.00 | -2.3 | |
| 10 | 1.00 | -6.0 | 5.88 | 175.0 | 0.01 | 84.7 | 1.01 | -6.0 | |
| 20 | 1.00 | -12.0 | 5.86 | 169.0 | 0.02 | 80.4 | 1.00 | -11.0 | |
| 30 | 0.99 | -17.9 | 5.74 | 164.0 | 0.03 | 74.8 | 1.00 | -17.2 | |
| 40 | 0.98 | -23.6 | 5.65 | 159.0 | 0.04 | 70.2 | 0.99 | -22.4 | |
| 50 | 0.98 | -29.3 | 5.55 | 154.0 | 0.04 | 65.6 | 0.98 | -27.3 | |
| 60 | 0.97 | -34.8 | 5.43 | 150.0 | 0.05 | 61.2 | 0.97 | -32.1 | |
| 70 | 0.96 | -40.1 | 5.31 | 145.0 | 0.06 | 56.9 | 0.96 | -36.8 | |
| 80 | 0.94 | -45.3 | 5.19 | 140.0 | 0.07 | 52.4 | 0.96 | -41.8 | |
| 90 | 0.93 | -50.3 | 5.03 | 135.0 | 0.07 | 47.9 | 0.94 | -46.9 | |
| 100 | 0.92 | -54.9 | 4.86 | 131.0 | 0.08 | 43.6 | 0.93 | -51.6 | |
| 125 | 0.89 | -65.5 | 4.42 | 122.0 | 0.09 | 34.7 | 0.89 | -61.6 | |
| 150 | 0.87 | -75.5 | 4.06 | 113.0 | 0.10 | 26.8 | 0.88 | -70.0 | |
| 175 | 0.85 | -84.2 | 3.71 | 105.0 | 0.10 | 19.0 | 0.86 | -78.2 | |
| 200 | 0.83 | -91.7 | 3.35 | 97.3 | 0.10 | 12.4 | 0.83 | -85.3 | |
| 250 | 0.82 | -105.0 | 2.81 | 84.6 | 0.11 | 1.2 | 0.82 | -96.8 | |
| 300 | 0.81 | -116.0 | 2.34 | 73.6 | 0.11 | -8.6 | 0.81 | -107.0 | |
| 350 | 0.81 | -125.0 | 2.00 | 64.0 | 0.10 | -16.7 | 0.82 | -115.0 | |
| 400 | 0.81 | -133.0 | 1.70 | 55.5 | 0.10 | -23.8 | 0.82 | -121.0 | |
| 450 | 0.82 | -140.0 | 1.48 | 47.7 | 0.09 | -30.2 | 0.83 | -128.0 | |
| 500 | 0.83 | -146.0 | 1.28 | 40.9 | 0.09 | -35.6 | 0.84 | -133.0 | |
| 600 | 0.86 | -157.0 | 1.00 | 29.0 | 0.08 | -44.9 | 0.87 | -142.0 | |
| 700 | 0.87 | -166.0 | 0.79 | 18.6 | 0.07 | -52.3 | 0.89 | -149.0 | |
| 800 | 0.89 | -175.0 | 0.64 | 9.8 | 0.06 | -58.1 | 0.90 | -155.0 | |
| 900 | 0.90 | 178.0 | 0.53 | 2.0 | 0.05 | -62.4 | 0.92 | -160.0 | |
| 1000 | 0.91 | 171.0 | 0.45 | -4.8 | 0.04 | -64.9 | 0.93 | -165.0 | |

Note

^{1.} For more extensive s-parameters see internet: http://www.semiconductors.philips.com/markets/communications/wirelesscommunication/broadcast.

UHF power MOS transistor

BLF542

BLF542 scattering parameters

 $V_{DS} = 28 \text{ V}; I_D = 50 \text{ mA.}; \text{ note 1}$

| f (MU=) | f (MHz) | | S ₁₁ S ₂₁ | | S ₁ | 12 | s ₂₂ | | |
|------------|-----------------|--------|---------------------------------|-------|-----------------|-------|-----------------|--------|--|
| 1 (IVITIZ) | s ₁₁ | ∠Φ | s ₂₁ | ∠Φ | s ₁₂ | ∠Φ | s ₂₂ | ∠Φ | |
| 5 | 1.00 | -4.1 | 12.20 | 177.0 | 0.00 | 0.0 | 0.99 | -3.2 | |
| 10 | 1.00 | -8.2 | 12.20 | 173.0 | 0.01 | 83.5 | 1.00 | -7.8 | |
| 20 | 0.99 | -16.3 | 12.10 | 167.0 | 0.02 | 78.1 | 0.99 | -14.5 | |
| 30 | 0.98 | -24.1 | 11.70 | 161.0 | 0.03 | 71.7 | 0.98 | -22.3 | |
| 40 | 0.97 | -31.7 | 11.40 | 155.0 | 0.03 | 66.2 | 0.96 | -28.8 | |
| 50 | 0.95 | -39.1 | 11.10 | 150.0 | 0.04 | 60.9 | 0.94 | -35.1 | |
| 60 | 0.93 | -46.1 | 10.70 | 144.0 | 0.05 | 55.8 | 0.93 | -41.1 | |
| 70 | 0.92 | -52.7 | 10.30 | 139.0 | 0.06 | 51.1 | 0.91 | -46.8 | |
| 80 | 0.90 | -59.1 | 9.92 | 134.0 | 0.06 | 46.2 | 0.89 | -52.7 | |
| 90 | 0.88 | -65.1 | 9.47 | 129.0 | 0.07 | 41.6 | 0.87 | -58.4 | |
| 100 | 0.86 | -70.3 | 9.00 | 125.0 | 0.07 | 37.3 | 0.85 | -63.6 | |
| 125 | 0.82 | -81.9 | 7.95 | 116.0 | 0.08 | 28.7 | 0.80 | -74.1 | |
| 150 | 0.80 | -92.5 | 7.12 | 107.0 | 0.08 | 21.2 | 0.78 | -82.8 | |
| 175 | 0.77 | -101.0 | 6.37 | 99.9 | 0.08 | 14.2 | 0.75 | -90.7 | |
| 200 | 0.75 | -109.0 | 5.68 | 93.5 | 0.08 | 8.5 | 0.73 | -97.4 | |
| 250 | 0.74 | -121.0 | 4.67 | 82.4 | 0.09 | -1.3 | 0.72 | -108.0 | |
| 300 | 0.73 | -130.0 | 3.87 | 72.9 | 0.08 | -9.4 | 0.71 | -116.0 | |
| 350 | 0.74 | -138.0 | 3.29 | 64.5 | 0.08 | -16.3 | 0.72 | -123.0 | |
| 400 | 0.75 | -145.0 | 2.81 | 57.2 | 0.08 | -22.2 | 0.73 | -129.0 | |
| 450 | 0.76 | -151.0 | 2.44 | 50.3 | 0.07 | -27.7 | 0.74 | -134.0 | |
| 500 | 0.77 | -156.0 | 2.13 | 44.2 | 0.07 | -32.2 | 0.75 | -138.0 | |
| 600 | 0.79 | -165.0 | 1.67 | 33.3 | 0.06 | -40.0 | 0.79 | -145.0 | |
| 700 | 0.82 | -173.0 | 1.34 | 23.6 | 0.05 | -46.1 | 0.82 | -152.0 | |
| 800 | 0.84 | 180.0 | 1.10 | 15.2 | 0.04 | -50.4 | 0.85 | -157.0 | |
| 900 | 0.86 | 173.0 | 0.92 | 7.5 | 0.04 | -52.9 | 0.87 | -162.0 | |
| 1000 | 0.87 | 167.0 | 0.78 | 0.7 | 0.03 | -52.8 | 0.88 | -166.0 | |

Note

^{1.} For more extensive s-parameters see internet: http://www.semiconductors.philips.com/markets/communications/wirelesscommunication/broadcast.

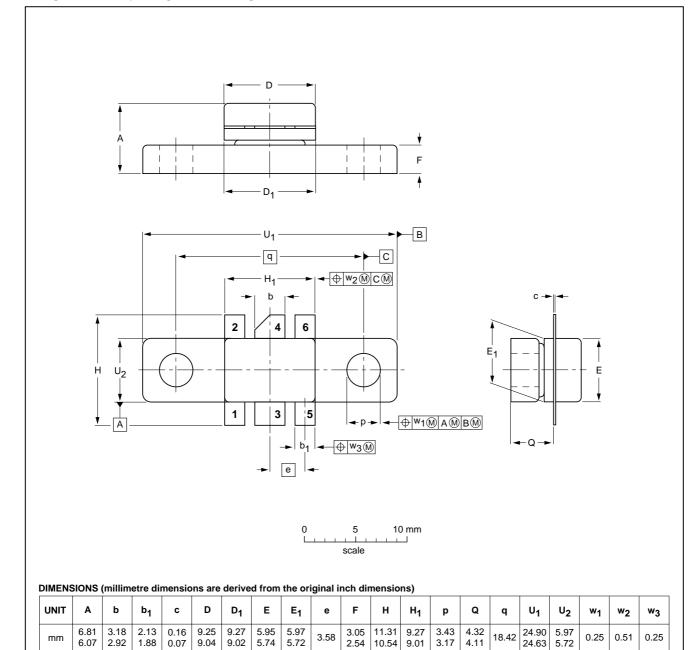
UHF power MOS transistor

BLF542

PACKAGE OUTLINE

Flanged ceramic package; 2 mounting holes; 6 leads

SOT171A



| OUTLINE | REFERENCES | | | | EUROPEAN | ISSUE DATE |
|---------|------------|-------|------|--|------------|------------|
| VERSION | IEC | JEDEC | EIAJ | | PROJECTION | ISSUE DATE |
| SOT171A | | | | | | 99-03-29 |

2.54

10.54

9.01

 0.120
 0.445
 0.365
 0.135
 0.170

 0.100
 0.415
 0.355
 0.125
 0.162

3.17

4.11

0.980 0.235 0.970 0.225

0.010 0.020 0.010

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0.07

9.04

 0.268
 0.125
 0.084
 0.006
 0.364
 0.365
 0.234
 0.235

 0.239
 0.115
 0.074
 0.003
 0.356
 0.355
 0.226
 0.225

9.02

UHF power MOS transistor

BLF542

DATA SHEET STATUS

| LEVEL | DATA SHEET STATUS ⁽¹⁾ | PRODUCT STATUS(2)(3) | DEFINITION |
|-------|-------------------------------------|-------------------------|--|
| I | Objective data | Development | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice. |
| II | Preliminary data | Qualification | This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product. |
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Notes

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- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

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Printed in The Netherlands

613524/03/pp15

Date of release: 2003 Sep 18

Document order number: 9397 750 11588

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